

<b>SANYO</b>	No.1685A	<b>2SA1423/2SC3656</b>
		PNP/NPN Epitaxial Planar Silicon Transistors
		<b>Switching Applications</b> (with Bias Resistor)

**Use**

. Switching circuit, inverter circuit, interface circuit, driver circuit.

**Features**

. With bias resistor (R1=10kΩ ,R2=10kΩ ).

( ): 2SA1423

**Absolute Maximum Ratings at Ta=25°C**

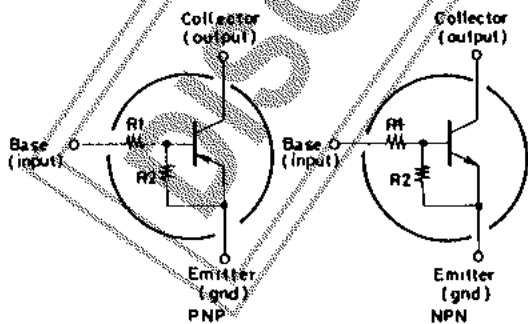
			unit
Collector to Base Voltage	V <sub>CB0</sub>	(-)50	V
Collector to Emitter Voltage	V <sub>CEO</sub>	(-)50	V
Emitter to Base Voltage	V <sub>EBO</sub>	(-)10	V
Collector Current	I <sub>C</sub>	(-)100	mA
Collector Current(Pulse)	I <sub>CP</sub>	(-)200	mA
Collector Dissipation	P <sub>C</sub>	400	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta=25°C**

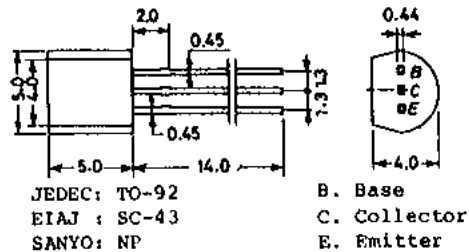
			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(-)0.1	μA
Collector Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> =(-)40V, I <sub>B</sub> =0			(-)0.5	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)5V, I <sub>C</sub> =0	(-)170	(-)250	(-)330	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)10mA	50			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)5mA		250		MHz
				(200)		
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		3.7		pF
				(5.5)		
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)10mA, I <sub>B</sub> =(-)0.5mA	(-)0.1	(-)0.3		V
Collector to Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =(-)10μA, I <sub>E</sub> =0	(-)50			V
Collector to Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =(-)100μA, R <sub>BE</sub> =∞	(-)50			V

Continued on next page.

**Electrical Connection**



**Case Outline 2003A**  
(unit:mm)



Specifications and information herein are subject to change without notice.

**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**  
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

Continued from preceding page.

			min	typ	max	unit
Input OFF-State Voltage	$V_{I(off)}$	$V_{CE}=(-)5V, I_C=(-)100\mu A$	(-)0.8	(-)1.1	(-)1.5	V
Input ON-State Voltage	$V_{I(on)}$	$V_{CE}=(-)0.2V, I_C=(-)10mA$	(-)1.0	(-)2.0	(-)4.0	V
Input Resistance	$R_1$		7.0	10	13	k $\Omega$
Resistance Ratio	$R_1/R_2$		0.9	1.0	1.1	-

Sample Application Circuit

